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HMC605LP3 / 605LP3E

GaAs PHEMT MMIC LOW NOISE AMPLIFIER w/ BYPASS MODE, 2.3 - 2.7 GHz

Typical Applications

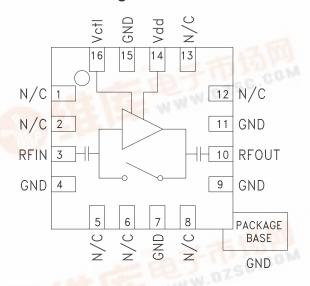
The HMC605LP3 / HMC605LP3E is ideal for:

- Wireless Infrastructure
- Customer Premise Equipment
- Fixed Wireless

dzsc.com

- WiMAX & WiBro
- Tower Mounted Amplifiers

Functional Diagram



Features

Noise Figure: 1.1 dB Output IP3: +31 dBm Gain: 20 dB Low Loss & Failsafe Bypass Path Single Supply: +3V or +5V 50 Ohm Matched Input / Output

General Description

The HMC605LP3 / HMC605LP3E are versatile, high dynamic range GaAs MMIC Low Noise Amplifiers that integrate a low loss LNA bypass path on the IC. The amplifier is ideal for WiBro & WiMAX receivers operating between 2.3 and 2.7 GHz and provides 1.1 dB noise figure, 20 dB of gain and +31 dBm output IP3 from a single supply of +5.0V @ 74 mA. Input and output return losses are 14 and 15 dB respectively with no external matching components required. A single control line (VctI) is used to switch between LNA mode and a low 2.0 dB loss bypass mode and reduces the current consumption to 10 μ A. The HMC605LP3 is failsafe and will default to the bypass mode with no DC power applied.

Parameter		LNA Mode			Bypass Mode			
			Тур.	Max.	Min.	Тур.	Max.	Units
Frequency Range		2	2.3 - 2.7		se F	2.3 - 2.7	150	GHz
Gain	17.5		20.5	181	-3.0	-2.0	0	dB
Gain Variation Over Temperature			0.012		-	0.002		dB / °C
Noise Figure	107.2		1.1	1.3				dB
Input Return Loss			14			13		dB
Output Return Loss 60			15			13		dB
Reverse Isolation			33					dB
Output Power for 1dB Compression (P1dB)*			17			16		dBm
Output Third Order Intercept (IP3)* (-20 dBm Input Power per tone, 1 MHz tone spacing)			31					dBm
Supply Current (Idd)			74	90		0.01		mA
LNA Mode to B	ypass Mode		-			6.0		ns
Swtiching Speed Bypass Mode to	LNA Mode		60			-		ns

Electrical Specifications, $T_A = +25^{\circ}$ C, Vdd = +5V

P1dB for LNA Mode is referenced to RFOUT while P1dB for Bypass Mode is referenced to RFIN.

For price, delivery, and to place orders, please contact Hittite Microwave Corporation

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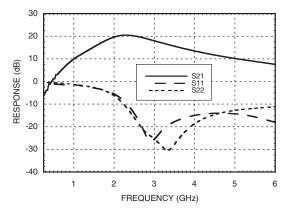


RoHS

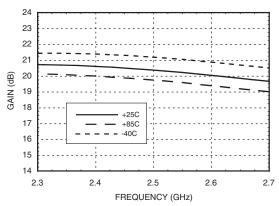
HMC605LP3 / 605LP3E

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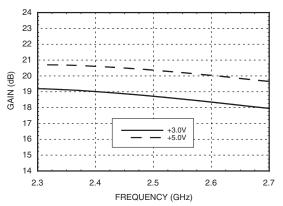
LNA Broadband Gain & Return Loss



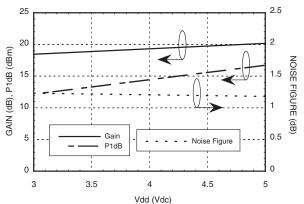
LNA Gain vs. Temperature



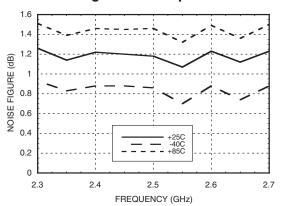
LNA Gain vs. Vdd



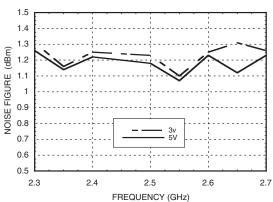
LNA – Gain, Noise Figure & Power vs. Supply Voltage @ 850 MHz



LNA Noise Figure vs. Temperature



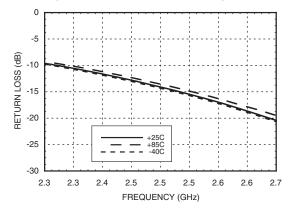
LNA Noise Figure vs. Vdd



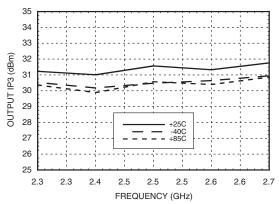


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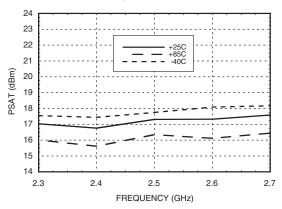
LNA Input Return Loss vs. Temperature



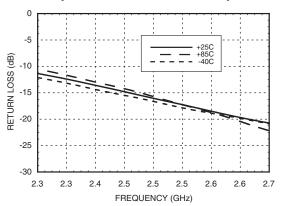
LNA Output IP3 vs. Temperature



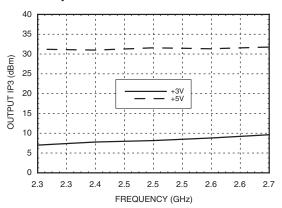
LNA Psat vs. Temperature



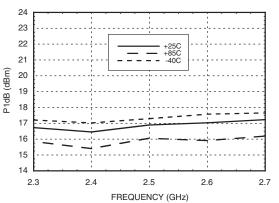
LNA Output Return Loss vs. Temperature



LNA Output IP3 vs. Vdd



LNA Output P1dB vs. Temperature



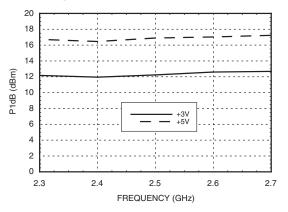
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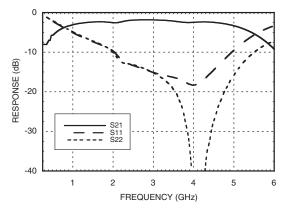


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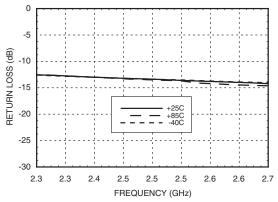
LNA Output P1dB vs. Vdd



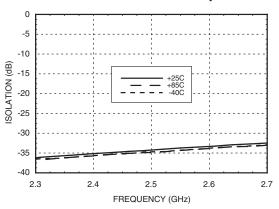
Bypass Mode Broadband Insertion Loss & Return Loss



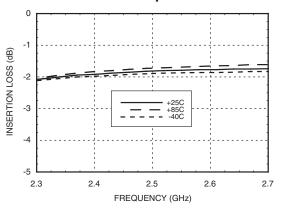
Bypass Mode Input Return Loss vs. Temperature

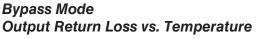


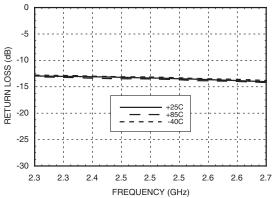
LNA Reverse Isolation vs. Temperature



Bypass Mode Insertion Loss vs. Temperature











Idd (mA)

74

Vctl = Vcc

Vctl= 0V

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Typical Supply Current vs. Vdd

Vdd (Vdc)

+5.0

LNA Mode

Bypass Mode

Truth Table

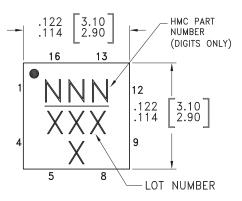
Absolute Maximum Ratings

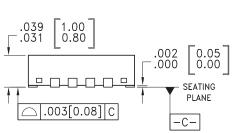
Drain Bias Voltage (Vdd)	+8.0 Vdc	
RF Input PowerLNA Mode(RFin)(Vdd = +5.0 Vdc)Bypass Mode	+15 dBm +30 dBm	
Channel Temperature	150 °C	
Continuous Pdiss (T = 85 °C) (derate 13.7 mW/°C above 85 °C)	890 mW	
Thermal Resistance (channel to ground paddle)	73 °C/W	
Storage Temperature	-65 to +150° C	
Operating Temperature	-40 to +85° C	

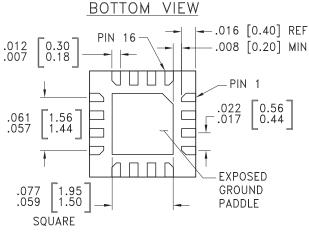


ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

Outline Drawing







NOTES:

- 1. LEADFRAME MATERIAL: COPPER ALLOY
- 2. DIMENSIONS ARE IN INCHES [MILLIMETERS]
- 3. LEAD SPACING TOLERANCE IS NON-CUMULATIVE
- 4. PAD BURR LENGTH SHALL BE 0.15mm MAXIMUM.
- PAD BURR HEIGHT SHALL BE 0.05mm MAXIMUM.
- 5. PACKAGE WARP SHALL NOT EXCEED 0.05mm.
- 6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.
- 7. REFER TO HITTITE APPLICATION NOTE FOR SUGGESTED LAND PATTERN.

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking ^[3]
HMC605LP3	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 ^[1]	605 XXXX
HMC605LP3E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 ^[2]	<u>605</u> XXXX

[1] Max peak reflow temperature of 235 °C

[2] Max peak reflow temperature of 260 °C

[3] 4-Digit lot number XXXX

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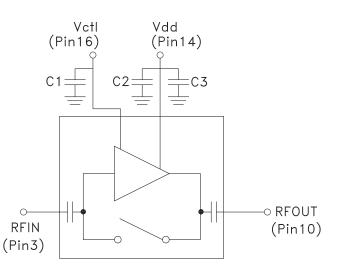
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Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 2, 5, 6, 8, 12, 13	N/C	No connection necessary. These pins may be connected to RF/DC ground.	
3	RFIN	This pin is AC coupled and matched to 50 Ohms. See application circuit.	
4, 7, 9, 11, 15	GND	These pins must be connected to RF/DC ground.	
10	RFOUT	This pin is AC coupled and matched to 50 Ohms.	
14	Vdd	Power supply voltage. Bypass capacitors are required. See application circuit.	
16	Vctl	Mode Control Voltage. See truth table.	Vctl O

Application Circuit

Components	Value
C1, C2	100pF
C3	10KpF



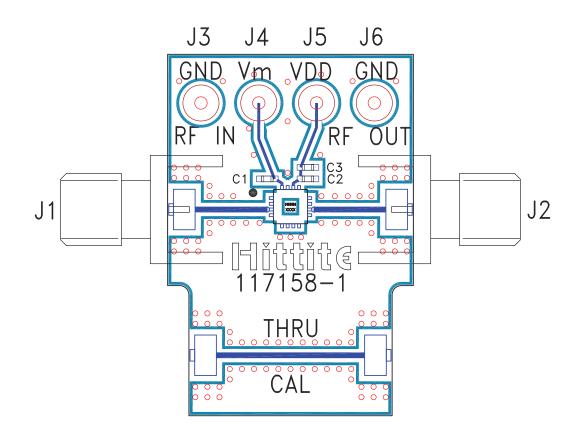
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Evaluation PCB



List of Materials for Evaluation PCB 117160 [1]

Item	Description
J1 - J2	PCB Mount SMA RF Connector
J3 - J6	DC Pin
C1, C2	100 pF Capacitor, 0402 Pkg.
C3	10 KpF Capacitor, 0402 Pkg.
U1	HMC605LP3 / HMC605LP3E Amplifier
PCB [2]	117158 Evaluation Board

Reference this number when ordering complete evaluation PCB
Circuit Board Material: Rogers 4350

The circuit board used in the final application should use RF circuit design techniques. Signal lines should have 50 ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation circuit board shown is available from Hittite upon request.



ROHS

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Notes:

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